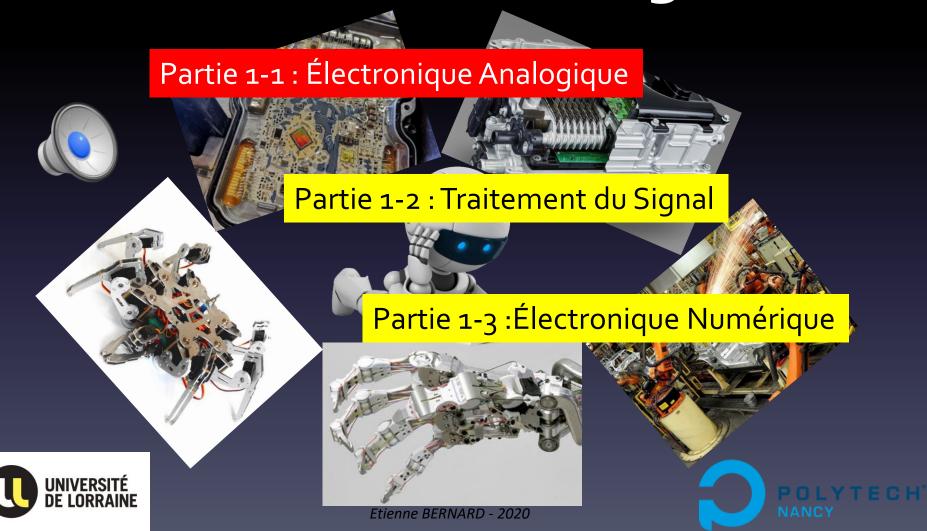
Partie 1 : Aspect électronique et traitement du signal





Partie 1 – 1 : L'Électronique analogique

Rappels:

4. - Représentation symbolique d'une tension

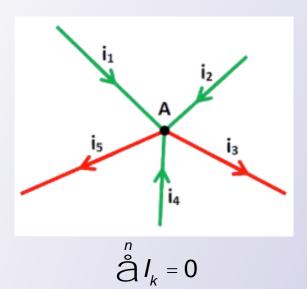




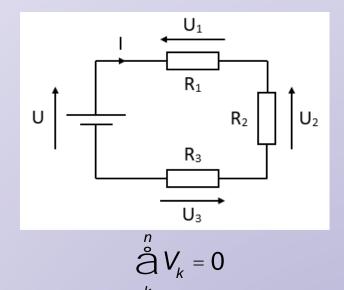


Lois de Kirchhoff

Lois des nœuds



- Lois des mailles



Autres méthodes d'analyse d'un circuit :

- Théorème de Thévenin
- Théorème de Norton



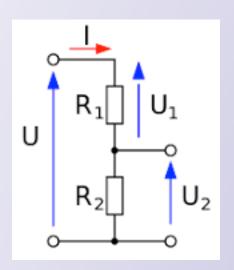


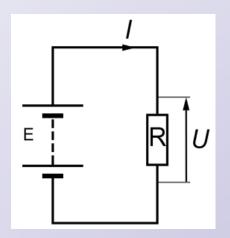


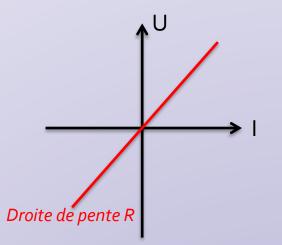
La résistance :

U = R . I

R en ohm (Ω)









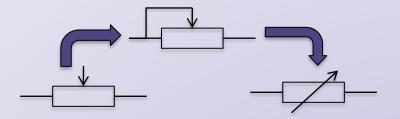
$$U_2 = U^* \frac{R_2}{R_1 + R_2}$$
 et $U_1 = U^* \frac{R_1}{R_1 + R_2}$







Le potentiomètre:

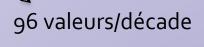


Les séries de valeurs normalisées pour les résistances

$$1,0-1,2-1,5-1,8-2,2-2,7-3,3-3,9-4,7-5,6-6,8-8,2$$

Série: E12 - E24 - E48 - E96

12 valeurs/décade 24 valeurs/décade



48 valeurs/décade





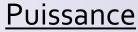


Marquage





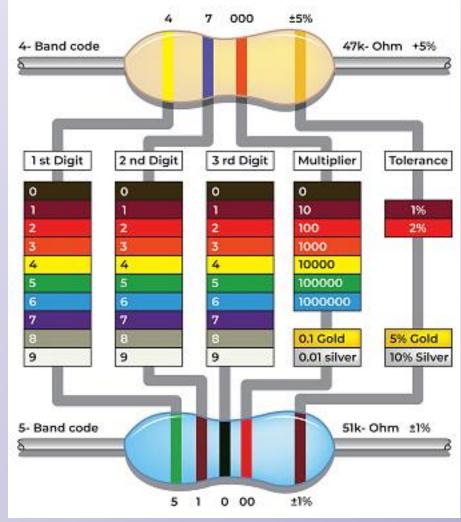




 $P = R \cdot I^2$







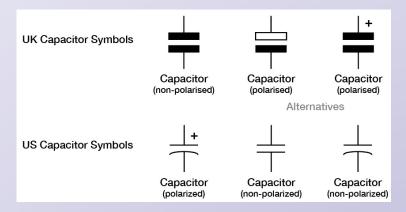




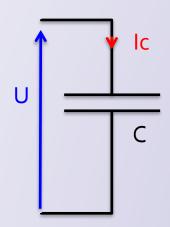


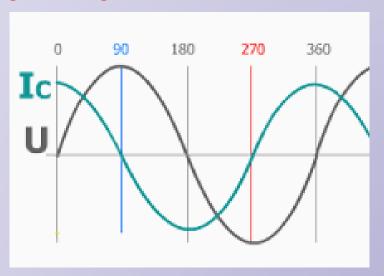
Le condensateur

$$I = C \cdot \frac{dV}{dt} \quad (1)$$



Condensateur → Elément de stockage d'énergie



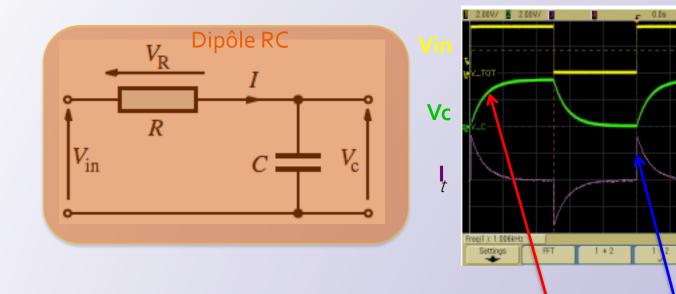








Le condensateur soumis à une tension constante



$$Vc = Vin.\left(1 - e^{-\frac{t}{t}}\right)$$
 avec $t = R \cdot C$



Lissage





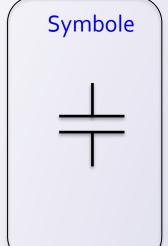


Les types de condensateurs

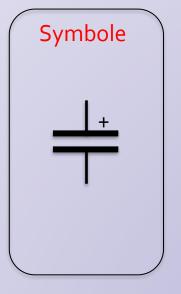
$$W = \frac{1}{2} \times C \times U^2$$

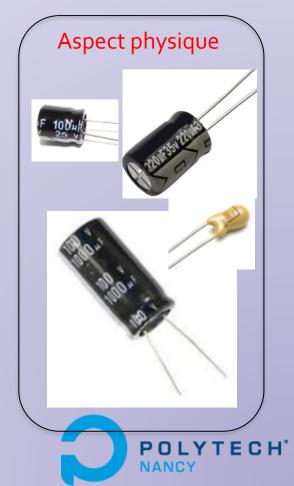
Non polarisés

<u>Polarisés</u>



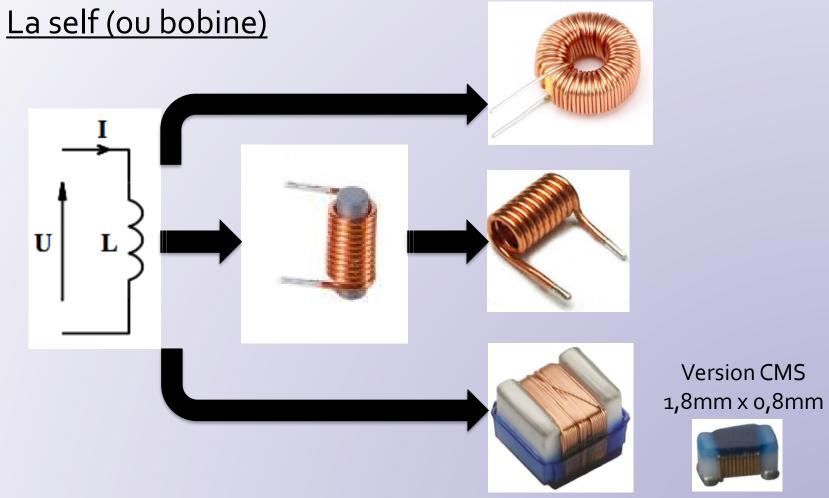










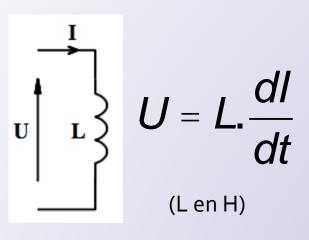


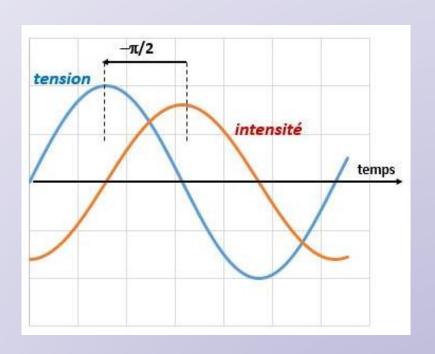






La self (ou bobine)





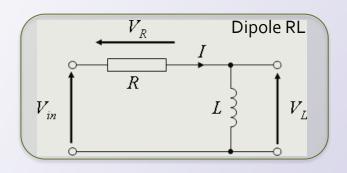
$$U = L \times \frac{dI}{dt} + r \times I$$
 avec r (résistance série du fil)







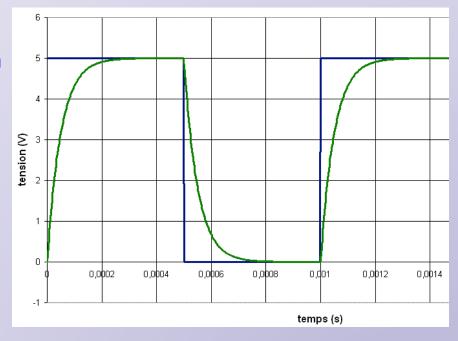
La self soumise à une tension constante



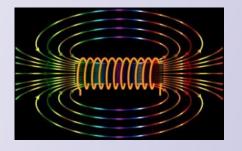
Vin

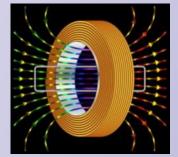
Image de I

$$I_L = \frac{Vin}{R} \cdot \left(1 - e^{-\frac{t}{t}}\right) \text{ avec } t = \frac{L}{R}$$



$$W = \frac{1}{2} \times L \times I^2$$





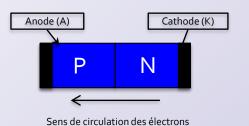
$$L = \frac{m_0 \times m_r \times N^2 \times S}{I}$$

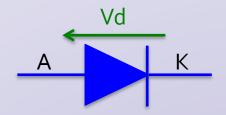


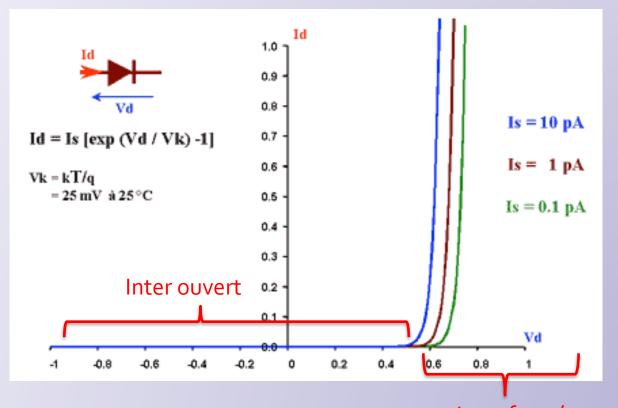




La diode





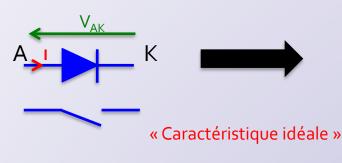


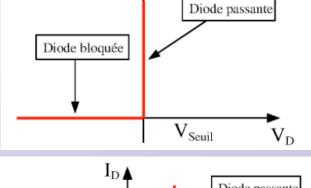




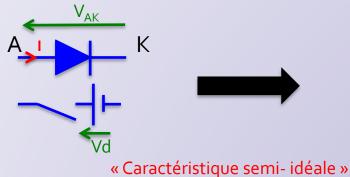


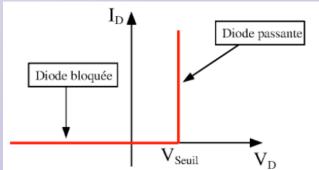
La diode

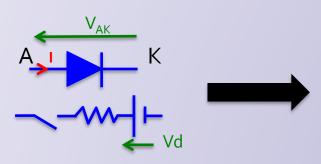


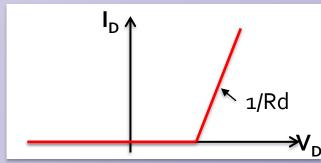


 $I_D \blacktriangle$









Si $I_D > 0$ alors $V_{AK} = V_D + R_D \times I_D$

« Caractéristique quasi-réelle »

NANCY

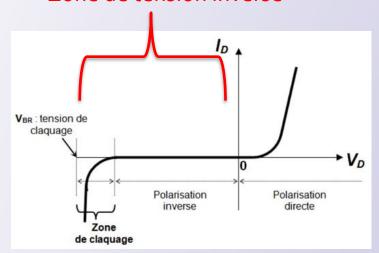


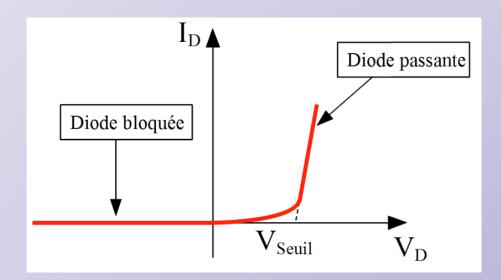


La diode réelle

$$I_D = I_S \left(e^{\left(\frac{Vd}{Vk} \right)} - 1 \right) \text{ avec } Vk = \frac{k \cdot T}{q} = 25mV \text{ à } 25^{\circ}C$$

Zone de tension inverse











Modèles de diode

CMS : Composant Monté en Surface

Version axiale

Version CMS

1N4148 Traitement du signal







Diode de redressement







Diode Schottky





Signal

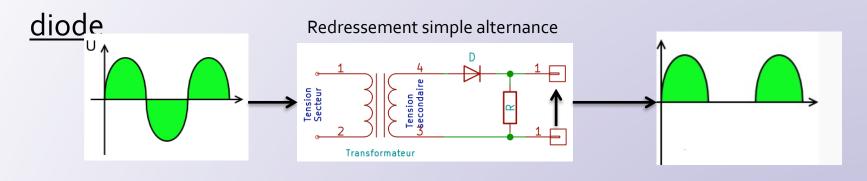


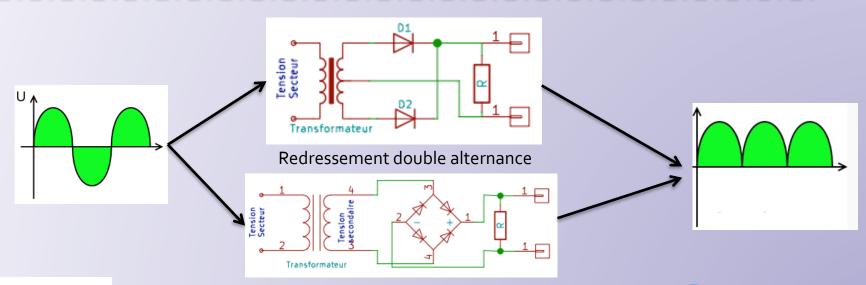






Applications de la



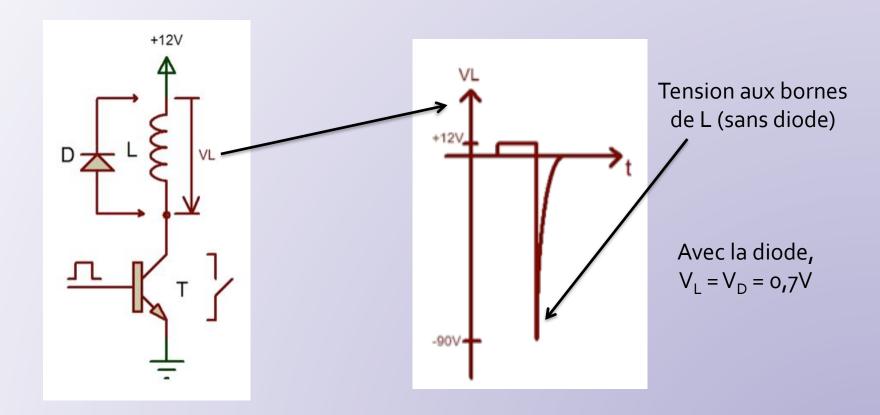








Autre application de la diode





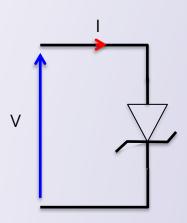


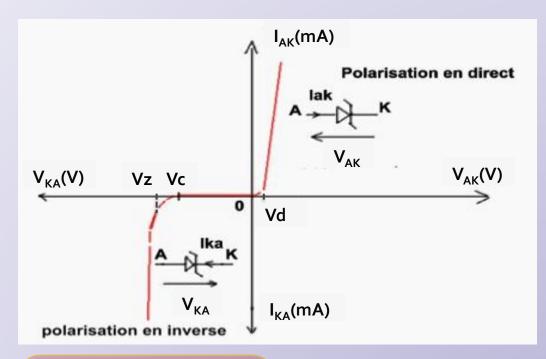


La diode Zener



Composant et symbole





$$Vc < V < Vd \Rightarrow I = 0$$

$$V > Vd \Rightarrow I \rightarrow \infty$$

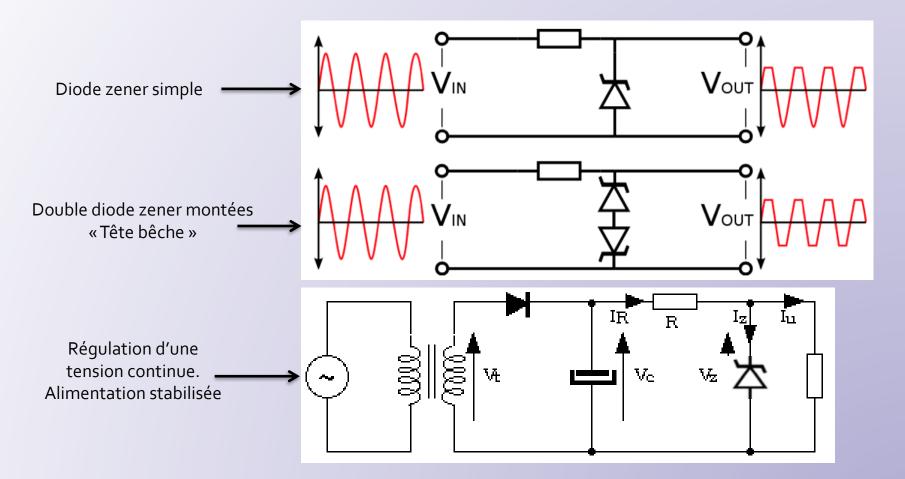
$$V < Vz \Rightarrow I \rightarrow -\infty$$







Utilisation de la diode Zener

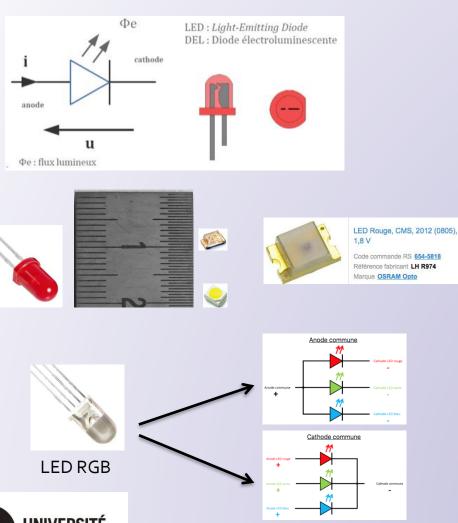


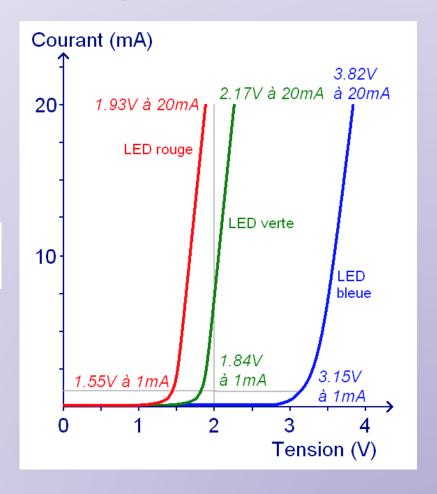






La diode électro-luminescente (LED – Light Emitting Diode)



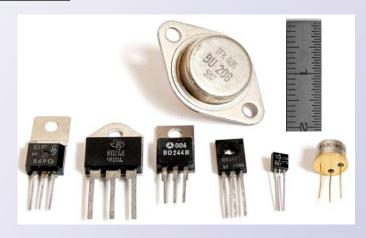








Le transistor



Le transistor bipolaire et ses symboles

Le transistor à effet de champ et ses symboles

Le transistor IGBT

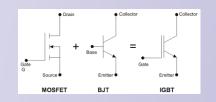
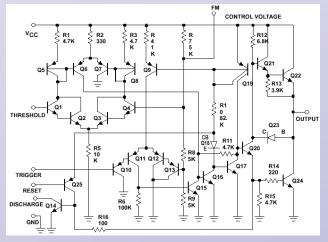
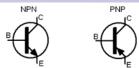
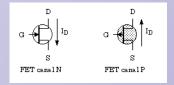


Schéma interne du NE555









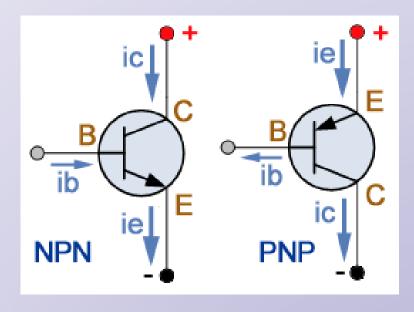




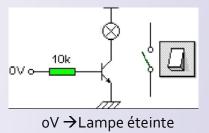
Le transistor bipolaire

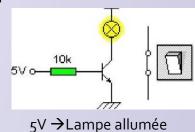
$$le = lc + lb$$
 avec $lc=b$. Ib d'où $le = lb \times (b + 1)$

 $β \rightarrow$ Gain en courant du transistor Si β grand alors le ≈ Ic

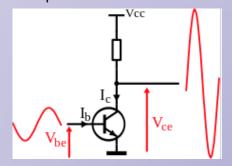


Transistor en interrupteur commandé



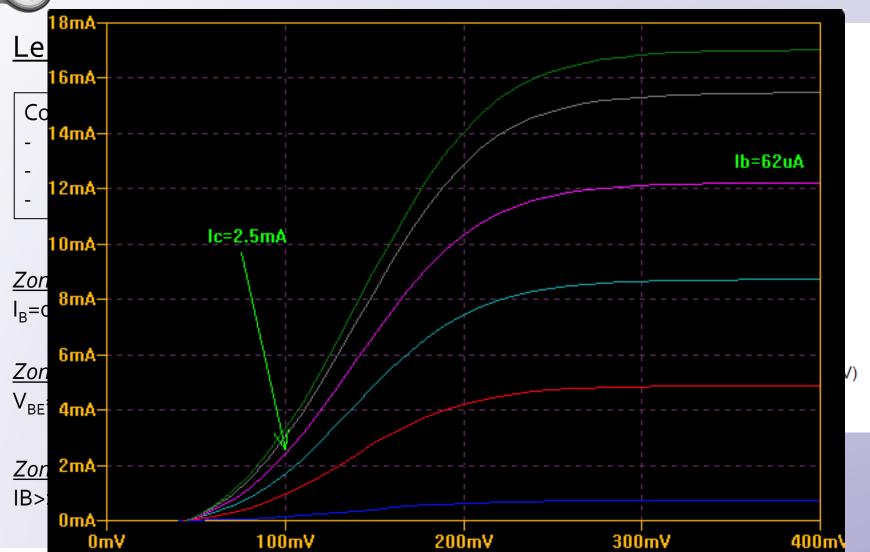


Amplificateur de courant







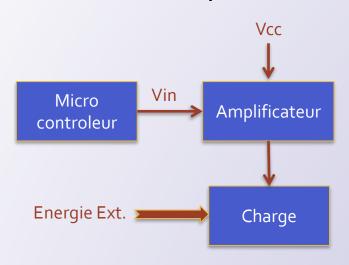


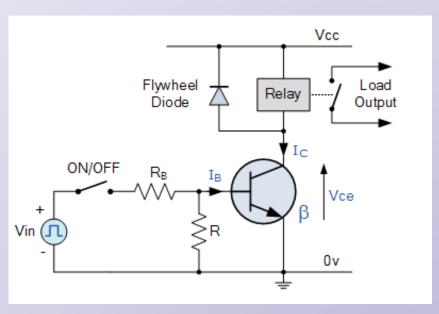






Le transistor bipolaire





Si Vin=oV \rightarrow I_B=o \rightarrow I_C= β .I_B=o \rightarrow Transistor bloqué \rightarrow Charge déconnectée

Si Vin=3,3V
$$\rightarrow$$
I_B>0 \rightarrow I_C= β .I_B \rightarrow V_{CE} \approx 0V \rightarrow Transistor saturé \rightarrow Relais activé \rightarrow Charge connectée

$$I_B = \frac{I_C}{b} = \frac{0.2}{200} = 1mA$$

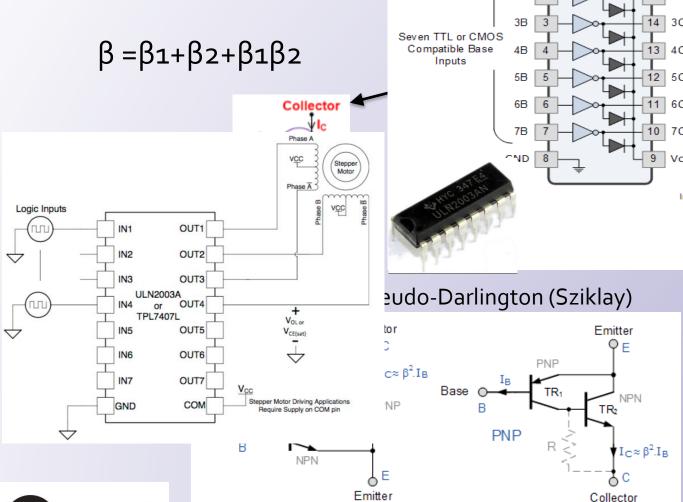
$$R_B = \frac{Vin - V_{BE}}{I_B} = \frac{3.3 - 0.7}{0.001} = 2.6KW$$

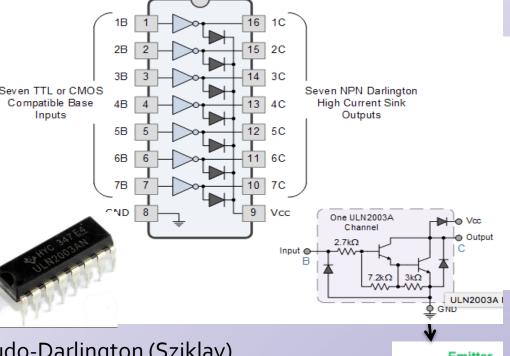


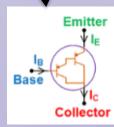




Le transistor bipolaire



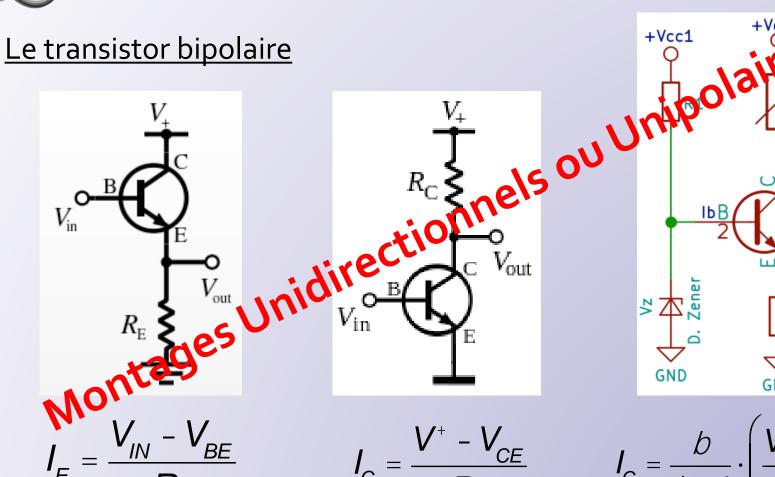




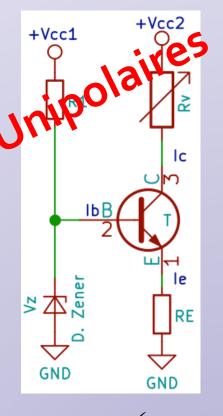








$$I_C = \frac{V^+ - V_{CE}}{R_C}$$



$$I_{C} = \frac{b}{b+1} \cdot \left(\frac{V_{Z} - V_{BE}}{R_{E}} \right)$$

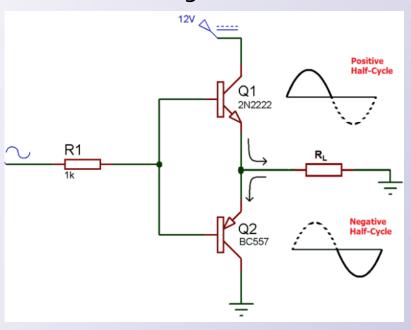




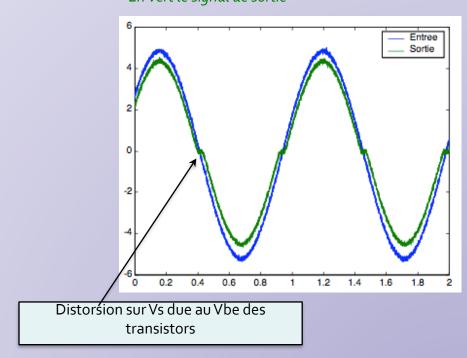


Le transistor bipolaire

Montage Push-Pull



En bleu le signal d'entrée En vert le signal de sortie



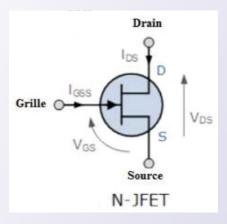


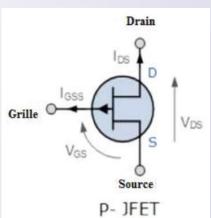


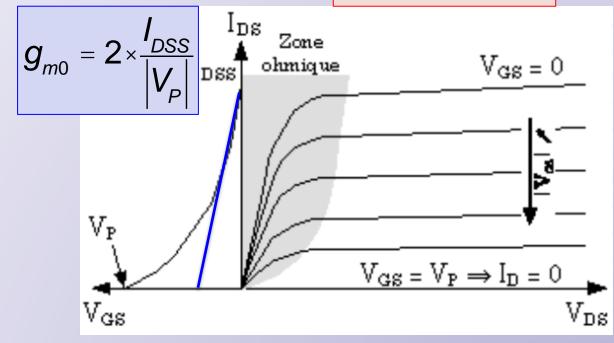


Le transistor à effet de champ (FET)

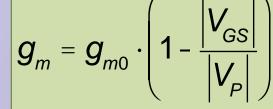
$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P} \right)^2$$







$$g_{m} = \frac{dI_{DS}}{dV_{GS}} = 2\frac{I_{DSS}}{|V_{P}|} \left(1 - \frac{|V_{GS}|}{|V_{P}|}\right)$$







Fin de la partie 1-1 : Électronique analogique

Pour toute question, n'hésitez pas à me contacter. Soit par mail : <u>etienne.bernard@univ-lorraine.fr</u> ou de vive voix à l'école - Bât.F – Bureau 210



